

AMENDMENTS TO THE SPECIFICATION:

Please replace the Abstract with the following amended Abstract:

A Schottky device having comprises a substrate layer of a first conductivity type having a surface, and a guard ring formed over the surface of the substrate layer and also surrounding a barrier region of the substrate layer. The guard ring has comprises a gate of a second conductivity type disposed over a dielectric layer. A metal can be formed over the barrier region to form a Schottky junction.